

40V, 120A N-CHANNEL POWER MOSFET

GENERAL DESCRIPTION

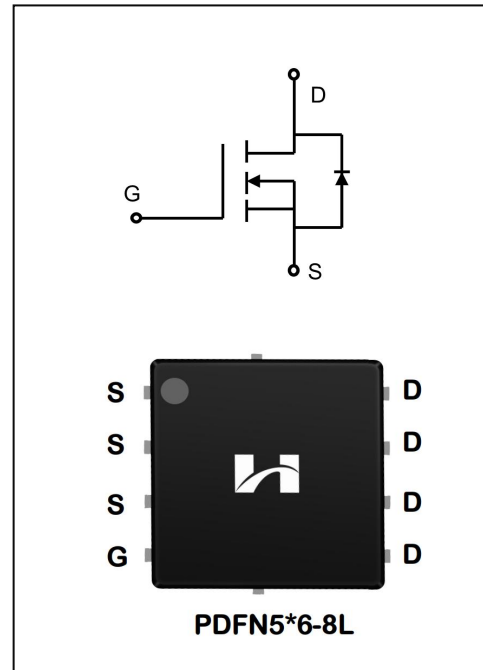
The SGM042R4T uses advanced SGT technology and design to provide excellent  $R_{DS(on)}$  with low gate charge. It can be used in a wide variety applications.

Features

- ◆  $V_{DS}=40V, I_D=120A$
- ◆  $R_{DS(on)}$   
 TYP:  $2.1m\Omega @V_{GS}=10V$   
 TYP:  $2.7m\Omega @V_{GS}=4.5V$

Applications

- ◆ Power faction correction (PFC)
- ◆ Switched mode power supplies (SMPS)
- ◆ Uninterruptible power supply (UPS)
- ◆ LED lighting power



ORDERING INFORMATION

Part No.	Package	Marking	Material	Packing
SGM042R4T	PDFN5*6-8L	SGM042R4T	Pb Free	Reel

## ABSOLUTE MAXIMUM RATINGS (T<sub>J</sub>=25°C unless otherwise noted)

Characteristics		Symbol	Ratings	Unit
Drain-Source Voltage		V <sub>DS</sub>	40	V
Gate-Source Voltage		V <sub>GS</sub>	±20	V
Drain Current	T <sub>C</sub> = 25°C	I <sub>D</sub>	120	A
	T <sub>C</sub> = 100°C		75	
Drain Current Pulsed(Note 1)		I <sub>DM</sub>	380	A
Power Dissipation(T <sub>C</sub> =25°C) -Derate above 25°C		P <sub>D</sub>	82	W
Single Pulsed Avalanche Energy (Note 2)		E <sub>AS</sub>	576	mJ
Operation Junction Temperature Range		T <sub>J</sub>	-55~+150	°C
Storage Temperature Range		T <sub>stg</sub>	-55~+150	°C
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		TL	300	°C

## THERMAL CHARACTERISTICS

Characteristics	Symbol	MAX	Unit
Thermal Resistance, Junction-to-Case	R <sub>θJC</sub>	1.6	°C/W
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub>	50	°C/W

## ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
Drain -Source Breakdown Voltage	B <sub>VDS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	40	--	--	V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V	--	--	1	μA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =20V, V <sub>DS</sub> =0V	--	--	100	nA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =-20V, V <sub>DS</sub> =0V	--	--	-100	
<b>On Characteristics</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> =250μA	1.2	1.7	2.2	V
Static Drain- Source On State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =30A	--	2.1	2.4	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A	--	2.7	3.6	
<b>Dynamic Characteristics</b>						
Gate Resistance	R <sub>g</sub>	V <sub>GS</sub> =0V; f=1.0MHZ	1	4	10	Ω
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =20V V <sub>GS</sub> =0V f=1.0MHZ	--	1840	--	pF
Output Capacitance	C <sub>oss</sub>		--	605	--	
Reverse Transfer Capacitance	C <sub>rss</sub>		--	25	--	
<b>Switching Characteristics</b>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =20V, V <sub>DS</sub> =10V R <sub>G</sub> =3Ω; I <sub>D</sub> =20A (Note 3.4)	--	25.4	--	ns
Turn-on Rise Time	t <sub>r</sub>		--	63.0	--	
Turn-off Delay Time	t <sub>d(off)</sub>		--	119.5	--	
Turn-off Fall Time	t <sub>f</sub>		--	89	--	

Total Gate Charge	$Q_g$	$V_{DS}=20V, I_D=20A$ $V_{GS}=10V$ (Note 3.4)	--	53	--	nc
Gate-Source Charge	$Q_{gs}$		--	12.6	--	
Gate-Drain Charge	$Q_{gd}$		--	9.2	--	

## SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	$I_S$	Integral Reverse P-N Junction Diode in the MOSFET	--	--	120	A
Pulsed Source Current	$I_{SM}$		--	--	380	
Diode Forward Voltage	$V_{SD}$	$I_S=40A, V_{GS}=0V$	--	0.85	1.2	V
Reverse Recovery Time	$T_{rr}$	$I_F=30A, V_R=10V,$ $dI_F/dt=100A/\mu S$	--	92	--	ns
Reverse Recovery Charge	$Q_{rr}$		--	15	--	nC

1. Pulse width limited by maximum junction temperature
2.  $L=0.5mH, V_{DD}=20V, V_G=10V, R_G=25\Omega$ , starting  $T_J=25^\circ C$
3. Pulse Test: Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$
4. Essentially independent of operating temperature

Typical Performance Characteristics

Figure 1. Output Characteristics

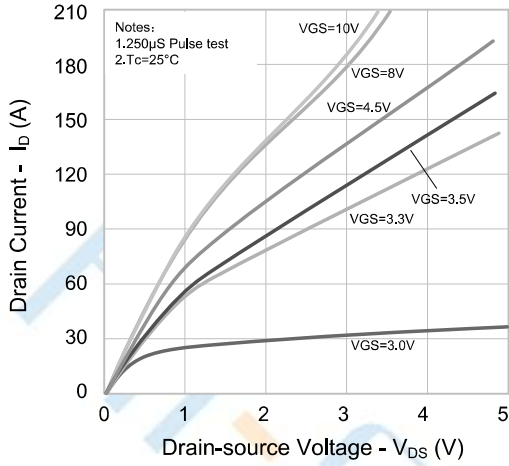


Figure 2. Transfer Characteristics

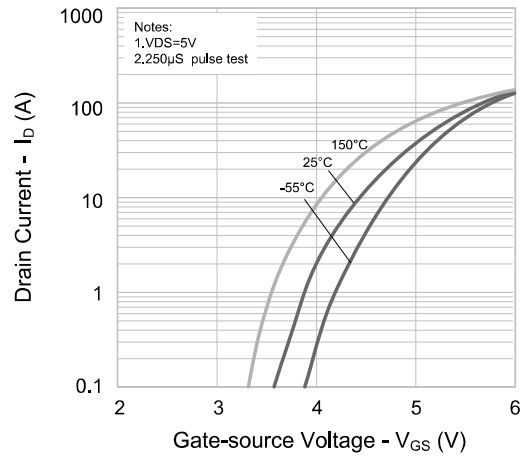


Figure 3. On-resistance vs. Drain Current

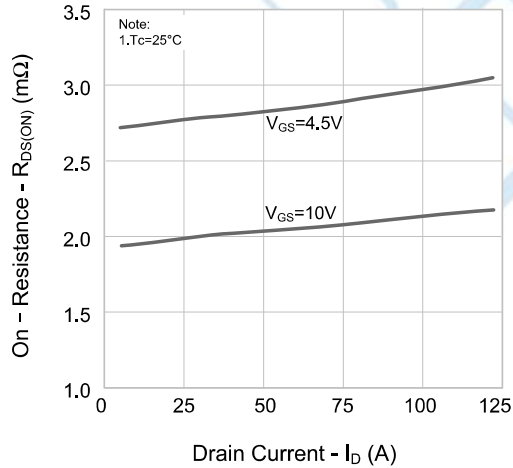


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

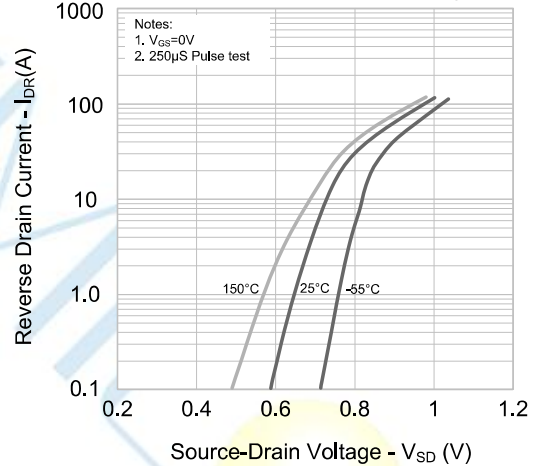


Figure 5. Capacitance Characteristics

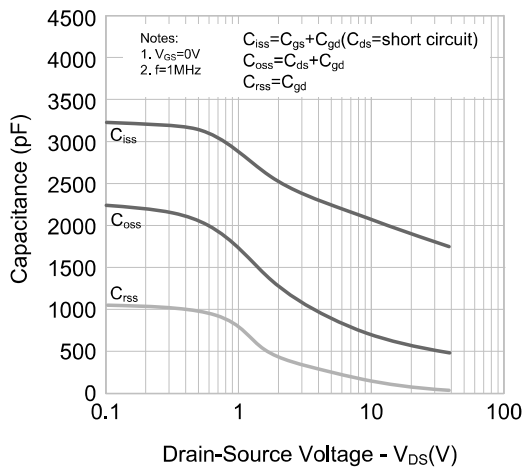
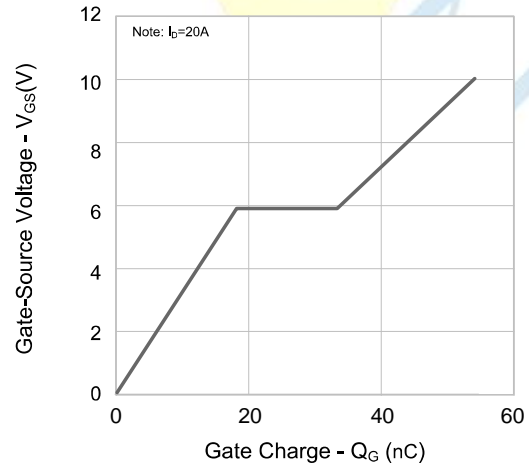


Figure 6. Gate Charge



Typical Performance Characteristics

Figure 7. Breakdown Voltage vs. Temperature Characteristics

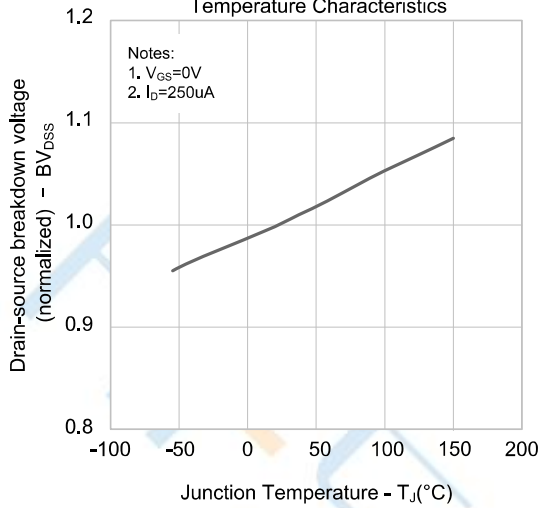


Figure 8. On-resistance vs. Temperature Characteristics

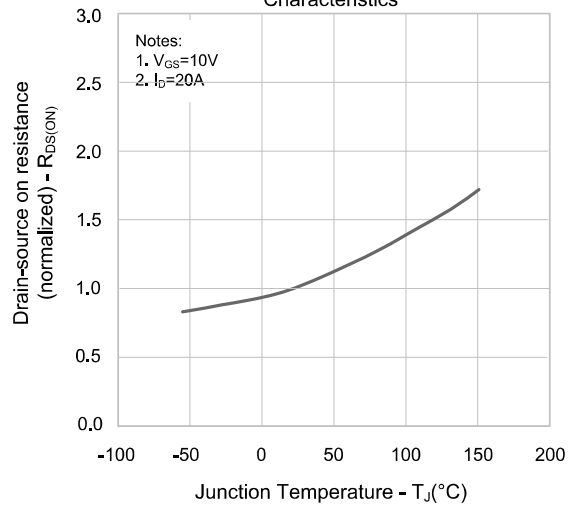
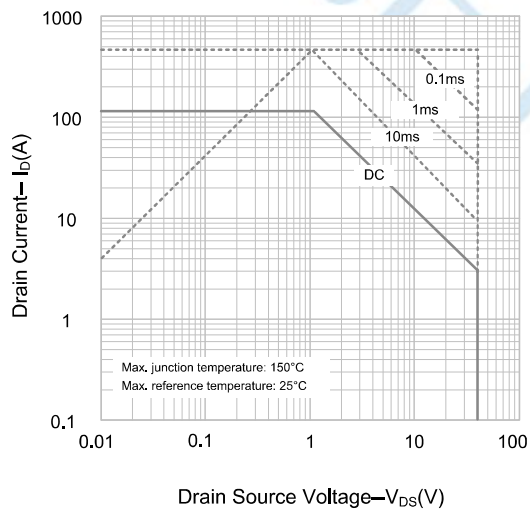
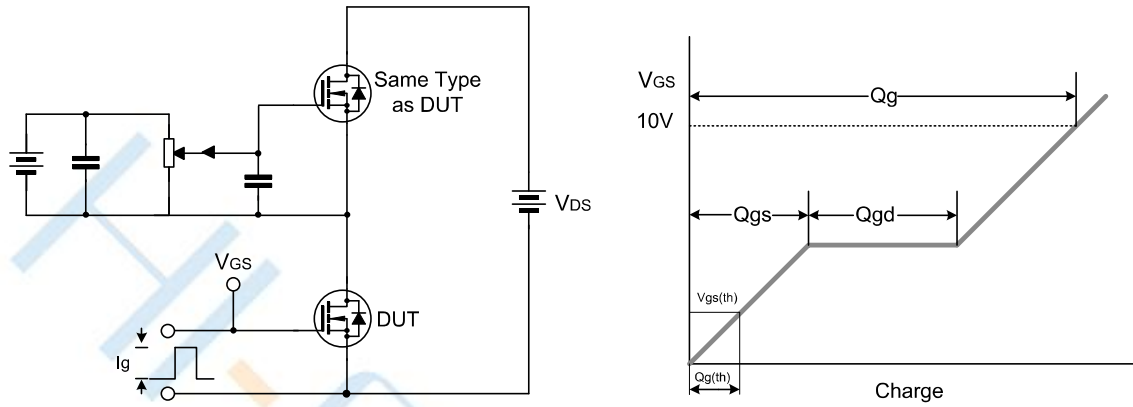


Figure 9. Max. Safe Operating Area

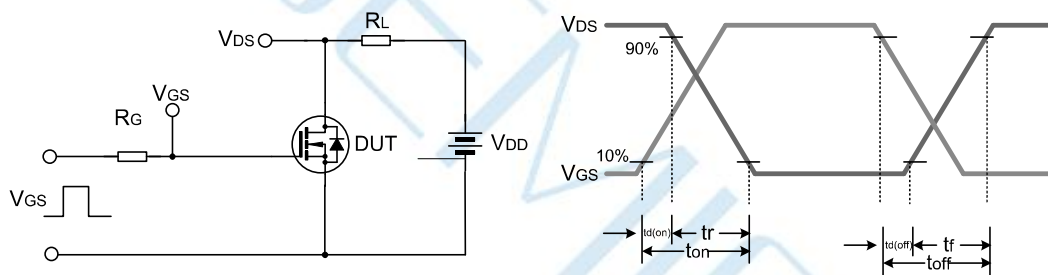


Test Circuit

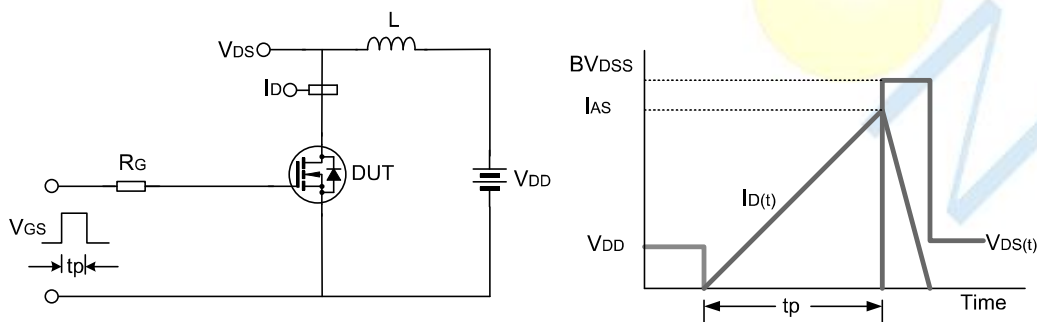
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveform

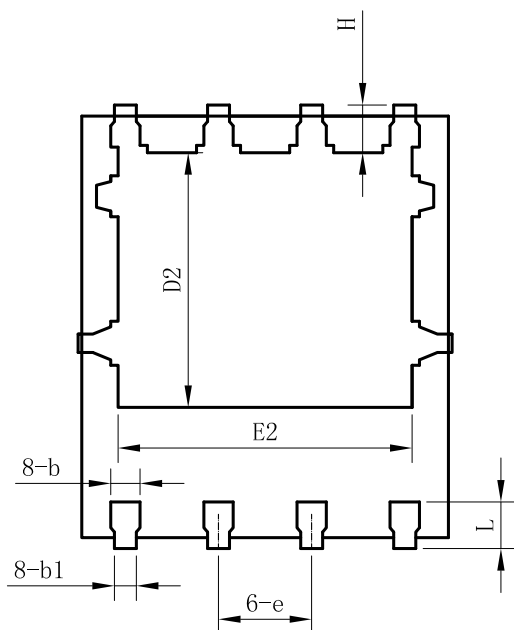
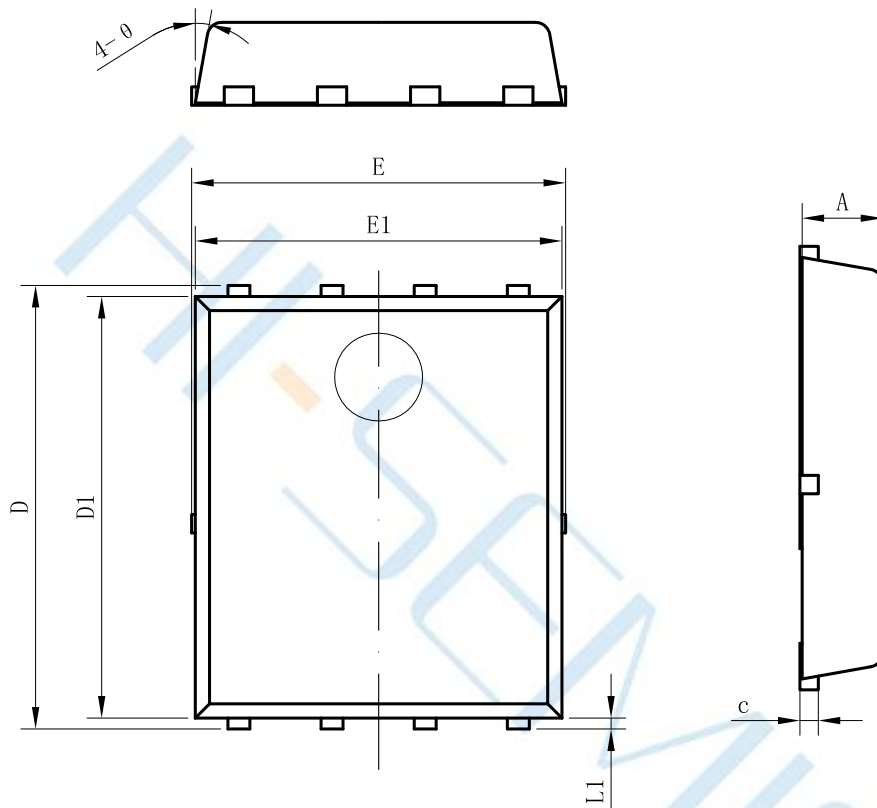


Unclamped Inductive Switching Test Circuit & Waveform



Package Dimensions of PDFN5\*6-8L

Unit:mm



COMMON DIMENSIONS  
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	1.0	1.1	1.2
b	0.35	0.4	0.45
b1		(0.3)	
c	0.2	0.25	0.35
D	5.9	6.05	6.2
D1	5.65	5.75	5.85
D2		(3.475)	
E			5.2
E1	4.9	5	5.1
E2		(4.01)	
e		1.27BSC	
H	0.5	0.65	0.75
L	0.51	0.635	0.75
L1		0.15	
θ		10°	

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